LATERAL PHASE CHANGE MEMORY AND METHOD THEREFOR

Abstract

Briefly, in accordance with an embodiment of the invention, a lateral phase change memory and a method to manufacture a phase change memory is provided. The method may include forming a conductor material over a substrate and patterning the conductor material to form two electrodes from the conductor material, wherein the two electrodes are separated by a sub-lithographic distance. The method may further include forming a phase change material between the two electrodes.